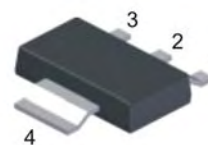


Features

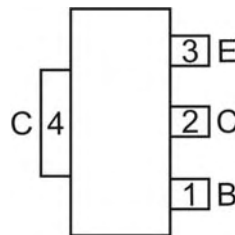
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT951)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

Mechanical Data

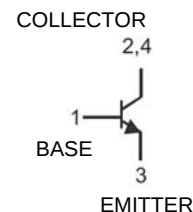
- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe
(Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



SOT-223



TOP VIEW



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	150	V
Collector-Emitter Voltage	V _{CE0}	60	V
Emitter-Base Voltage	V _{EB0}	6	V
Continuous Collector Current	I _C	6	A
Power Dissipation	P _{tot}	1(Note 3) 3(Note 4)	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.
 4. The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	150	—	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	60	—	—	V	I _C = 10mA*, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6	—	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	50 1	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	—	—	10	nA	V _{EB} = 6V, I _C = 0
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	50 100 170 375	mV	I _C = 0.1A, I _B = 5mA* I _C = 1A, I _B = 50mA* I _C = 2A, I _B = 50mA* I _C = 6A, I _B = 300mA*
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	1200	mV	I _C = 6A, I _B = 300mA*
Base-Emitter Turn-On Voltage	V _{BE(ON)}	—	—	1150	mV	I _{CE} = 6A, V _{CE} = 1V*
DC Current Gain	h _{FE}	100 100 75 25	—	— 300 —	—	I _C = 10mA, V _{CE} = 1V* I _C = 2A, V _{CE} = 1V* I _C = 5A, V _{CE} = 1V* I _C = 10A, V _{CE} = 1V*
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	—	130	—	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Output Capacitance	C _{obo}	—	45	—	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on} t _{off}	—	45 1100	—	ns	I _C = 1A, I _{B1} = 100mA I _{B2} = 100mA, V _{CC} = 10V

* Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%

Typical Characteristics @T_{amb} = 25°C unless otherwise specified

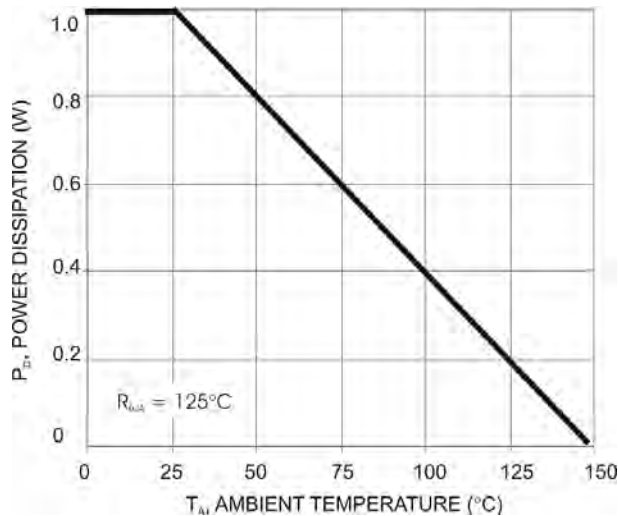


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

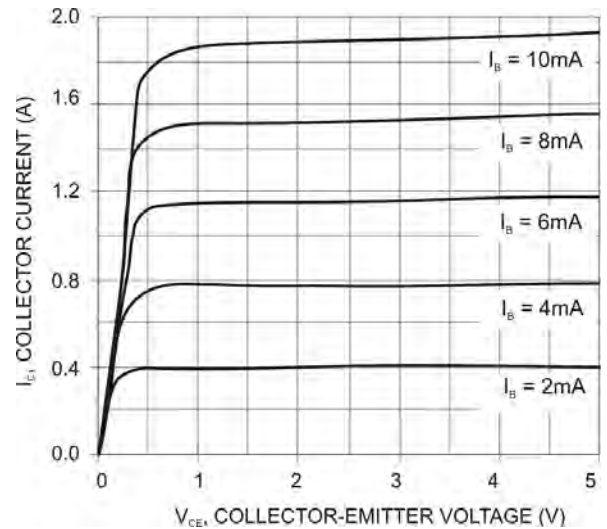


Fig. 2 Collector Current vs. Collector Emitter Voltage

Notes: 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.

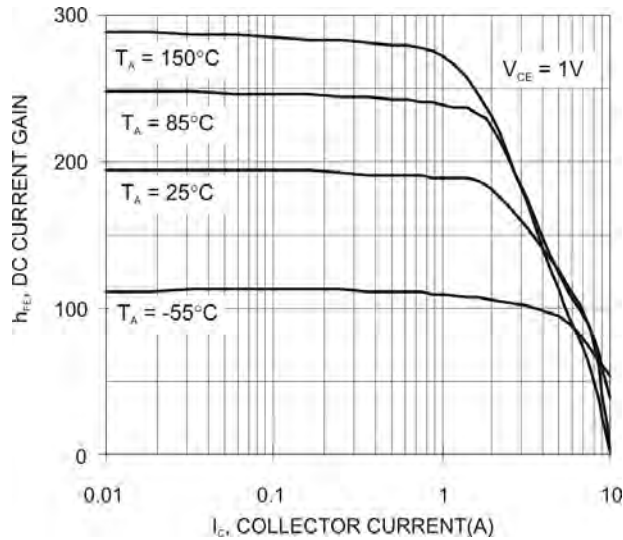


Fig. 3 Typical DC Current Gain vs. Collector Current

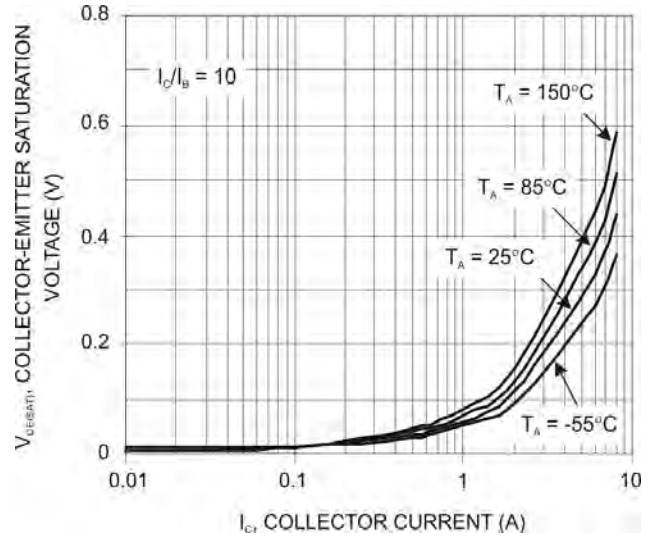


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

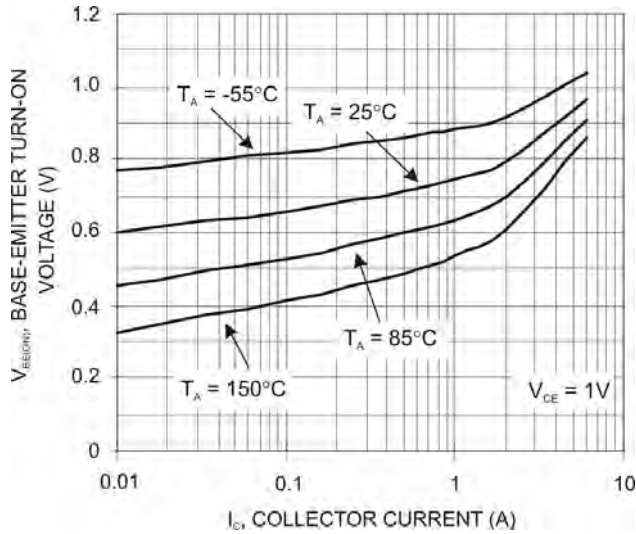


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

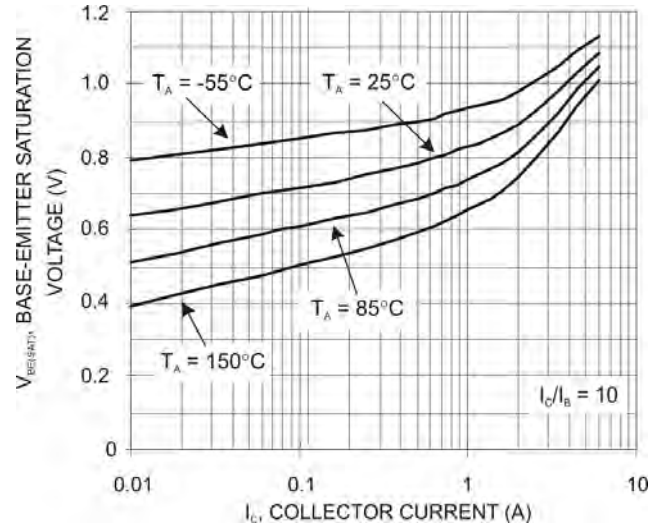


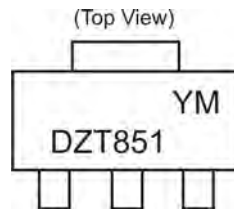
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZT851-13	SOT-223	2500/Tape & Reel

Notes: 5. Packaging Details as shown on page 4, or go to our website at <http://www.diodes.com/ap2007.pdf>.

Marking Information



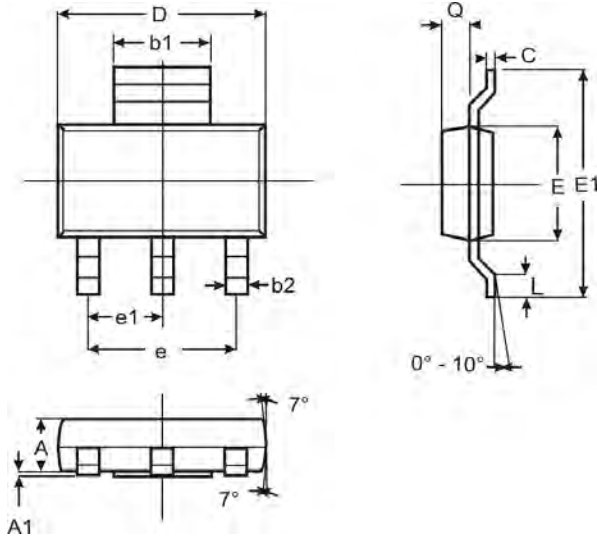
DZT851 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

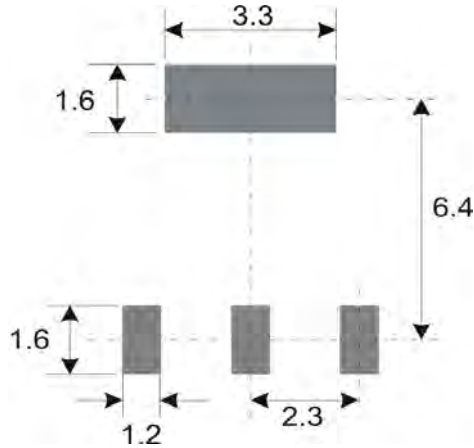
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout: (Based on IPC-SM-782)



(Unit:mm)

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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